

捷多邦N587505柱Tru TN582305

SURFACE MOUNT VOIDLESS-HERMETICALLY SEALED FAST RECOVERY GLASS RECTIFIERS

		DESC	RIPT						APPEAR	ANCE
PRF-19500 be tolerate reverse vol constructio also availa separate d other rectii recovery tii through-ho	0/429 and is d. These in ltages from 2 n using an i ble in axial- lata sheet for fier products me speed re le and surface	rface mount rect ideal for high-re idustry-recognize 200 to 1000 volts internal "Categor leaded package or 1N5615 thru is to meet high equirements inclu- ce mount package current data, consu	tifier dio eliability ed 1.0 <i>A</i> s are he ry l" me e config 1N5623 er and uding fa ges.	de serie applica amp rate tallurgic urations 3). Micr lower ast and u	ations where ed rectifiers lly sealed w al bond. Th for thru-hol rosemi also current ratir ultrafast dev	a failu for worl ith void hese de e mour offers i ngs with ice type	re canno king pea ess-glas evices ar nting (se numerou h variou es in bot	ot ss e e is is th	Package or D-1	e "A"
		EATURES						ICATIONS /	BENEFIT	S ^{O M}
 Surface mount package series equivalent to the JEDEC registered 1N5615 to 1N5623 series Voidless hermetically sealed glass package Triple-Layer Passivation Internal "<i>Category I</i>" Metallurgical bonds Working Peak Reverse Voltage 200 to 1000 Volts. JAN, JANTX, JANTXV, and JANS available per MIL-PRF-19500/429 Axial-leaded equivalents also available (see separate data sheet for 1N5615 thru 1N5623) 					 Fast recovery 1 Amp rectifiers 200 to 1000 V Military and other high-reliability applications General rectifier applications including bridges, half- bridges, catch diodes, etc. High forward surge current capability Extremely robust construction Low thermal resistance Controlled avalanche with peak reverse power capability Inherently radiation hard as described in Microsemi MicroNote 050 					
	ΜΑΧΙ	MUM RATIN	GS					ANICAL AND	PACKAG	ING
 Junction & Storage Temperature: -65°C to +175°C Thermal Resistance: 7°C/W junction to end cap Thermal Impedance: 4.5°C/W @ 10 ms heating time Average Rectified Forward Current (I₀): 1.0 Amps @ T_A = 55°C Forward Surge Current: 30 Amps @ 8.3 ms half-sine Solder Temperatures: 260°C for 10 s (maximum) 				me 3 @	 CASE: Hermetically sealed voidless hard glass with Tungsten slugs TERMINATIONS: End caps are Copper with Tin/Lead (Sn/Pb) finish. Note: Previous inventory had solid Silver end caps with Tin/Lead (Sn/Pb) finis MARKING & POLARITY: Cathode band only TAPE & REEL option: Standard per EIA-481-B WEIGHT: 193 mg See package dimensions and recommended pad layout on last page 					
ELECTR	ICAL CHA	ARACTERIST	ICS							
TYPE	WORKING PEAK REVERSE VOLTAGE V _{RWM}	BREAKDOWN VOLTAGE V _{BR} @ 50µA	RECT CURE I _o @ (NOT	RENT T _A TE 1)	FORWAR D VOLTAGE (MAX.) V _F @ 3A	CURI (M/ I _R @	ERSE RENT AX.) V _{RWM}	CAPACITANCE (MAX.) C @ V _R =12 V f=1 MHz	SURGE CURRENT I _{FSM} (NOTE 2)	RECOVER (MAX.) (NOTE 3) t _{rr}
	VOLTS	VOLTS			VOLTS		A	pF	AMPS	ns
1N5615US 1N5617US 1N5619US 1N5621US	200 400 600 800	220 440 660 880	50°C 1.00 1.00 1.00 1.00	100°C .750 .750 .750 .750 .750	.8 MIN.	25°C .5 .5 .5 .5	100°C 25 25 25 25 25	45 35 25 20	25 25 25 25 25	150 150 250 300

NOTE 3: $I_F = 0.5A$, $I_{RM} = 1A$, $I_{R(REC)} = 0.250 A$

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1N5615US - 1N5623US



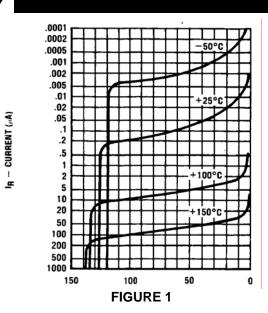
1N5615US thru 1N5623US

SURFACE MOUNT VOIDLESS-HERMETICALLY SEALED FAST **RECOVERY GLASS RECTIFIERS**

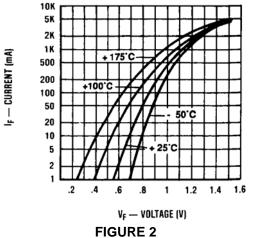
SYMBOLS & DEFINITIONS					
Symbol	Definition				
V _{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current				
V _{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range				
Ι _Ο	Average Rectified Output Current: Output Current averaged over a full cycle with a 50 hZ or 60 Hz sine-wave input and a 180 degree conduction angle				
V _F	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current				
I _R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature				
С	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage				
t _{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs.				

GRAPHS





TYPICAL REVERSE CURRENT vs V_R



TYPICAL FORWARD VOLTAGE vs FORWARD CURRENT

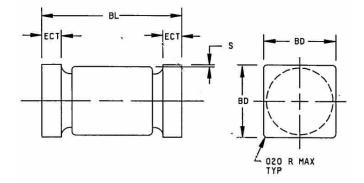




1N5615US thru 1N5623US

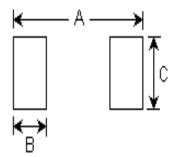
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PACKAGE DIMENSIONS AND PAD LAYOUT



NOTE: This Package Outline has also previously been identified as "D-5A"

	INC	HES	mm		
	MIN	MAX	MIN	MAX	
BD	.097	.103	2.46	2.62	
BL	.185	.200	4.70	5.08	
ECT	.019	.028	0.48	0.71	
S	.003		0.08		



PAD LAYOUT

	INCHES	mm
Α	0.246	6.25
В	0.067	1.70
С	0.105	2.67

Note: If mounting requires adhesive separate from the solder, an additional 0.060 inch diameter contact may be placed in the center between the pads as an optional spot for cement.